Silicon NPN Power Transistors 2SC1826

DESCRIPTION

·With TO-220 package
·Collector current :I_C=4A
·Collector power dissipation
:P_C=30W@T_C=25□

APPLICATIONS

·For use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

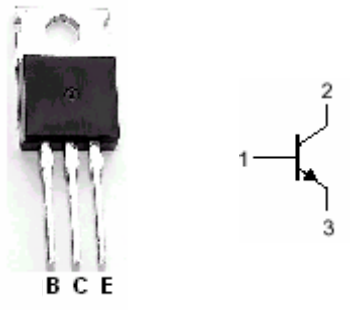

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	80	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		4	A
P_C	Collector power dissipation	T_C=25□	30	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA ;I_B=0	60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ;I_E=0	80			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A; I_B=0.3A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A ;I_B=0.3A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=80V;I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=4V	40		320	
f_T	Transition frequency	I_C=0.5A ; V_{CE}=12V		10		MHz

PACKAGE OUTLINE

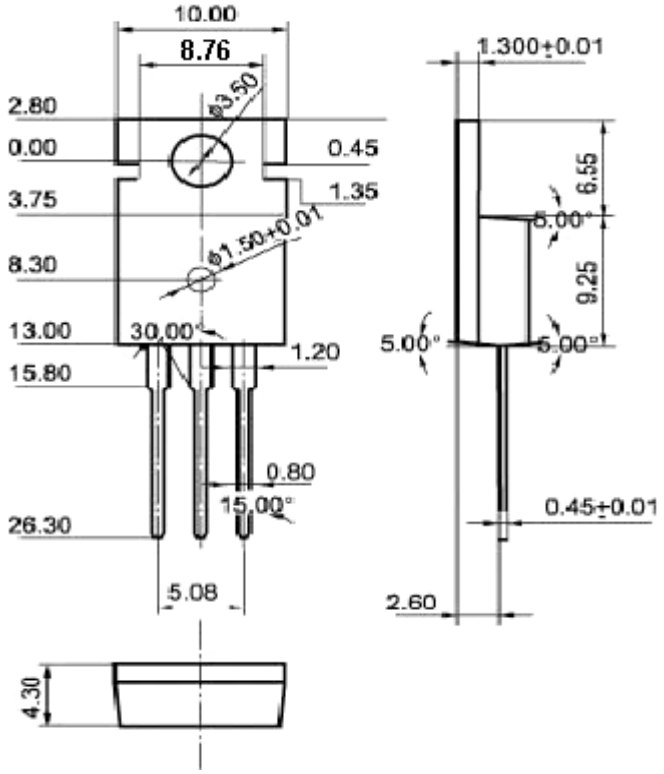

Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)